

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 81-84 and 91. Please amend claim 85 as follows:

Listing of Claims:

1-84. (Cancelled)

85. (Currently Amended) A method of forming a semiconductor package assembly, conductively isolating modules within an integrated circuit package assembly, comprising:

forming a capacitor within the semiconductor package assembly, the capacitor having a first terminal and a second terminal;

coupling a ground plane of a first module to the first terminal of the capacitor; and

coupling a ground plane of a second module to the second terminal of the capacitor; and

wherein the assembly further comprises a substrate having a first side and an opposing second side, and wherein forming a capacitor within the semiconductor package assembly further comprises forming the capacitor adjacent to the first side, and attaching the first and second modules to the second side.

86-89. (Cancelled)

90. (Previously Presented) The method of claim 85, wherein the assembly further comprises a substrate having a first side and an opposing second side, and wherein forming a capacitor within the semiconductor package assembly further comprises forming the capacitor adjacent to the first side, and attaching the first and second modules to the first side.

91. (Cancelled)

92. (Previously Presented) The method of claim 85, wherein the assembly further comprises a substrate and the modules have first and opposing second sides, and further wherein forming the capacitor within the semiconductor package assembly comprises forming the capacitor proximate to the opposing second sides of the modules.

93. (Previously Presented) The method of claim 85, wherein the assembly further comprises a first and a second substrate, the first module being attached to the first substrate and the second module being attached to the second substrate, and wherein forming the capacitor within the semiconductor package assembly further comprises forming the capacitor between the first module and the second module.